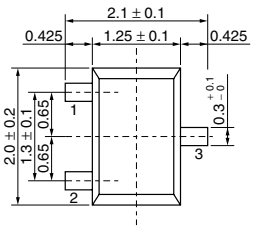
查询MA3J744供应商

MA3J744

Silicon epitaxial planar type

For super-high speed switching circuit
For small current rectification

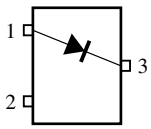
Unit : mm



1 : Anode
2 : NC
3 : Cathode
EIAJ : SC-70
Flat S- Mini Type Package (3-pin)

Marking Symbol: M1M

Internal Connection



■ Features

- Small S-mini type package allowing high-density mounting
- Allowing to rectify under ($I_{F(AV)}$ = 200 mA) condition

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}$	200	mA
Peak forward current	I_{FM}	300	mA
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

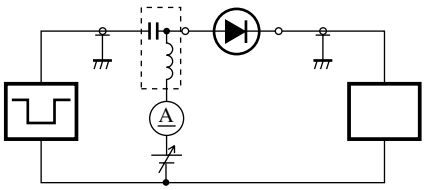
Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

■ Electrical Characteristics T_a = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	V_R = 30 V			50	μA
Forward voltage (DC)	V_F	I_F = 200 mA			0.55	V
Terminal capacitance	C_t	V_R = 0 V, f = 1 MHz		30		pF
Reverse recovery time*	t_{rr}	$I_F = I_R$ = 100 mA I_{rr} = 10 mA, R_L = 100 Ω		3		ns

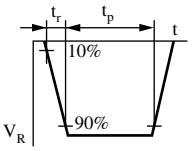
Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.
2. Rated input/output frequency: 1 000 MHz
3. * : t_{rr} measuring instrument

Bias Application Unit N-50BU



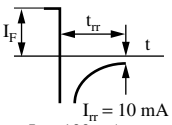
Pulse Generator (PG-10N) R_s = 50 Ω
W.F.Analyzer (SAS-8130) R_i = 50 Ω

Input Pulse



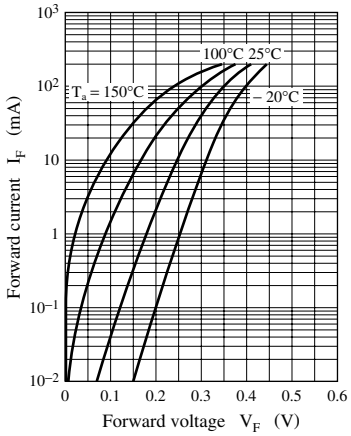
t_p = 2 μs
t_r = 0.35 ns
δ = 0.05

Output Pulse

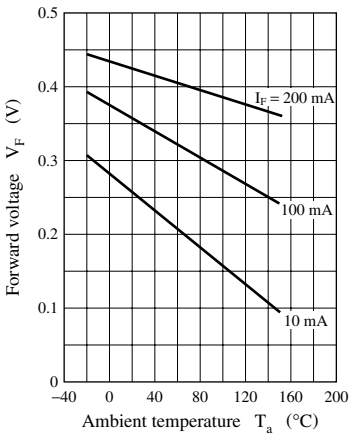


I_F = 100 mA
I_R = 100 mA
R_L = 100 Ω

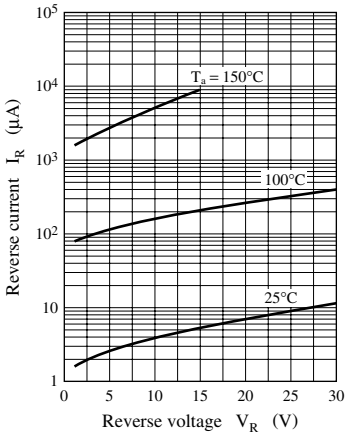
I_F — V_F



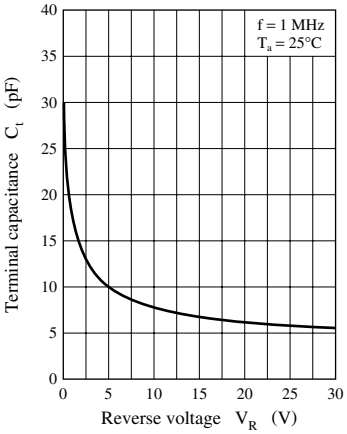
V_F — T_a



I_R — V_R



C_t — V_R



I_R — T_a